

isc N-Channel MOSFET Transistor

2SK2662

• FEATURES

- Drain Current $I_D = 5A @ T_C = 25^\circ C$
- Drain Source Voltage-
: $V_{DSS} = 500V(\text{Min})$
- Low leakage current
- High forward transfer admittance
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

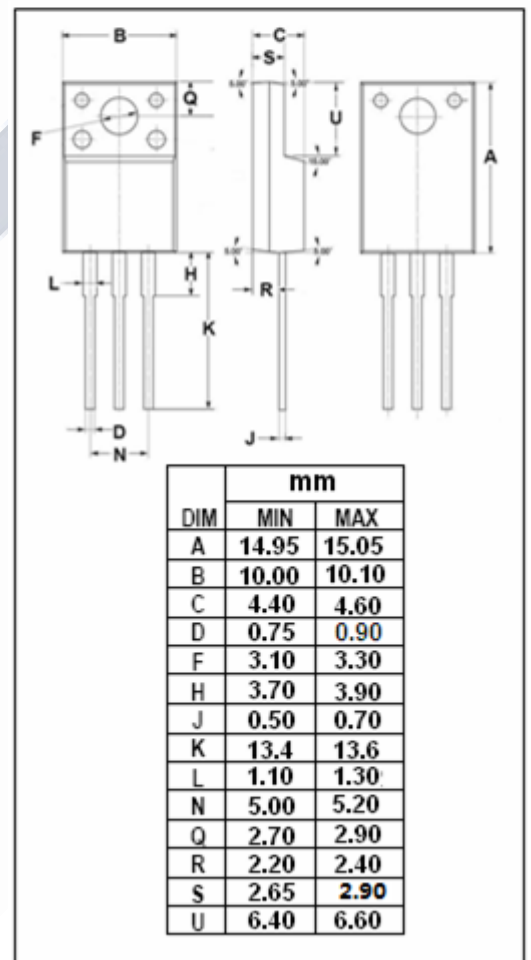
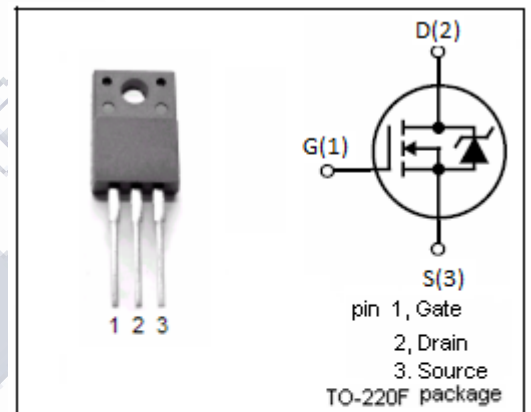
- DC-DC converter, Relay Drive and motor Drive Application

• ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	500	V
V_{GS}	Gate-Source Voltage-Continuous	± 30	V
I_D	Drain Current-Continuous	5	A
P_D	Total Dissipation @ $T_C = 25^\circ C$	35	W
T_j	Max. Operating Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature	-55~150	$^\circ C$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	3.57	$^\circ C/W$
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	62.5	$^\circ C/W$



isc N-Channel MOSFET Transistor**2SK2662****• ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0; I_D=10\text{mA}$	500			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=10\text{V}; I_D=1\text{mA}$	2.0		4.0	V
V_{DSF}	Forward voltage(Diode)	$I_{DR}=5\text{A}; V_{GS}=0$			1.7	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}; I_D=2.5\text{A}$		1.35	1.50	Ω
I_{GSS}	Gate-Body Leakage Current	$V_{GS}=\pm 25\text{V}; V_{DS}=0$			± 10	μA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}; V_{GS}=0$			100	μA